

IN THE CLAIMS:

Please amend the claims as follows:

1. (Currently amended) A pattern formation method comprising the steps of:

forming a resist film of a chemically amplified resist material including a base polymer, an acid generator for generating an acid through irradiation with light and ~~lactone~~ a material having negative polarity;

performing pattern exposure by selectively irradiating said resist film with exposing light while supplying ~~a solution~~ an immersion solution onto said resist film; and

forming a resist pattern by developing said resist film after the pattern exposure.

2. (Currently amended) The pattern formation method of Claim 1,

wherein said material having negative polarity ~~lactone~~ is ~~mevalonic~~ lactone, γ -butyrolactone, γ -valerolactone or δ -valerolactone, carbohydrate lactone, sultone, carbohydrate sultone, sultine, carbohydrate sultine, or a polymer containing lactone, sulfine, or sulton.

3. (Currently amended) The pattern formation method of Claim 1,

wherein said material having negative polarity is included a carboxyl group or a sulfonyl group. ~~solution is water.~~

4. (Currently amended) The pattern formation method of Claim 1,

wherein said immersion solution is ~~perfluoropolyether~~ water.

5. (Currently amended) ~~The~~ A pattern formation method of claim 1, comprising the steps of:

wherein said immersion solution is perfluoropolyether.

~~forming a resist film of a chemically amplified resist material including a base polymer,
an acid generator for generating an acid through irradiation with light and a polymer containing
lactone;~~

~~performing pattern exposure by selectively irradiating said resist film with exposing light
while supplying a solution onto said resist film; and~~

~~forming a resist pattern by developing said resist film after the pattern exposure.~~

6. (Currently amended) The pattern formation method of Claim 5 1,

wherein said exposing light is KrF excimer laser, ArF excimer laser, F₂ laser, KrAr laser,
or Ar₂ laser. ~~lactone is mevalonic lactone, γ butyrolactone, γ valerolactone or δ valerolactone.~~

7. (Currently amended) The pattern formation method of Claim 5 2,

wherein said ~~polymer for containing~~ said lactone is melavonic lactone, γ -butyrolactone, γ -
valerolactone or δ -valerolactone. ~~poly(acrylic ester) or poly(methacrylic ester).~~

8. (Currently amended) The pattern formation method of Claim 5 2,

wherein said polymer containing said lactone, said sultone, or said sultine is poly(acrylic
ester) or poly(methacrylic ester). ~~solution is water.~~

9. (Currently amended) The pattern formation method of Claim 5 2,

wherein said carbohydrate lactone is D-gluconic acid δ -lactone, β -D-glucofurannurone
acid γ -lactone or L-mannal acid di- γ -lactone. ~~solution is perfluoropolyether.~~

10. (Currently amended) The A pattern formation method of claim 2, comprising the
steps of:

wherein said sultone is pentane-2, 5-sultone or naphthalene-1, 8-sultone.

~~forming a resist film of a chemically amplified resist material including a base polymer,
an acid generator for generating an acid through irradiation with light and carbohydrate lactone;
performing pattern exposure by selectively irradiating said resist film with exposing light
while supplying a solution onto said resist film; and~~

~~forming a resist pattern by developing said resist film after the pattern exposure.~~

11. (Currently amended) The pattern formation method of Claim 10 2,

wherein said sultine is 3H-2, 1-benzoxathiol=1-oxide. ~~carbohydrate lactone is D-gluconic
acid δ -lactone, β -D-glucofurannurone acid γ -lactone or L-mannal acid di γ -lactone.~~

Claims 12-21 (Canceled)